# VS-ST230SPbF Series

**Vishay Semiconductors** 

# **Phase Control Thyristors** (Stud Version), 230 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	230 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1400 V, 1600 V				
V <sub>TM</sub>	1.55 V				
I <sub>GT</sub>	150 mA				
TJ	-40 °C to +125 °C				
Package	TO-93 (TO-209AB)				
Circuit configuration	Single SCR				

### **FEATURES**

- Center amplifying gate
- International standard case TO-93 (TO-209AB)
- · Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **TYPICAL APPLICATIONS**

- DC motor controls
- · Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I		230	А			
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C			
I <sub>T(RMS)</sub>		360	А			
1	50 Hz	5700	٨			
ITSM	60 Hz	5970	A			
l <sup>2</sup> t	50 Hz	163	kA <sup>2</sup> s			
14	60 Hz	149	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		1400 to 1600	V			
tq	Typical	100	μs			
TJ		-40 to +125	C°			

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE R	ATINGS			
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$
VS-ST230S	14	1400	1500	30
V3-312303	16	1600	1700	30



COMPLIANT

# **VS-ST230SPbF Series**



Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS		
Maximum average on-state current	l=	180° condu	180° conduction, half sine wave		230	А		
at case temperature	I <sub>T(AV)</sub>		ction, nan sine (	wave	85	°C		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 78 °C	case temperat	ure	360			
		t = 10 ms	No voltage		5700			
Maximum peak, one-cycle	<b>I</b>	t = 8.3 ms	reapplied		5970	Α		
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		4800			
		t = 8.3 ms	reapplied	Sinusoidal half wave,	5000			
Maximum 12t far fusian	l <sup>2</sup> t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	163	kA <sup>2</sup> s		
		t = 8.3 ms	reapplied		148			
Maximum I <sup>2</sup> t for fusing		1-1			t = 10 ms	100 % V <sub>RRM</sub>		115
		t = 8.3 ms	reapplied		105			
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	e reapplied	1630	kA²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$ ), $T_{J} = T_{J}$ maximum	0.92	V		
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), $T_J = T_J maxin$	num	0.98	v		
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum	0.88	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.81	11152		
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 720 A,	$T_J = T_J maximu$	ım, t <sub>p</sub> = 10 ms sine pulse	1.55	V		
Maximum holding current	Ι <sub>Η</sub>	T _ 25 °C	anada ayanlıy 1	2.V registive load	600	mA		
Maximum (typical) latching current	١L	1j=25 C,	anoue supply 1	2 V resistive load	1000 (300)	IIIA		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \le 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0	110
Typical turn-off time	tq	$I_{TM}$ = 300 A, $T_J$ = $T_J$ maximum, dI_F/dt = 20 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA





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TRI	GG	ER	ING
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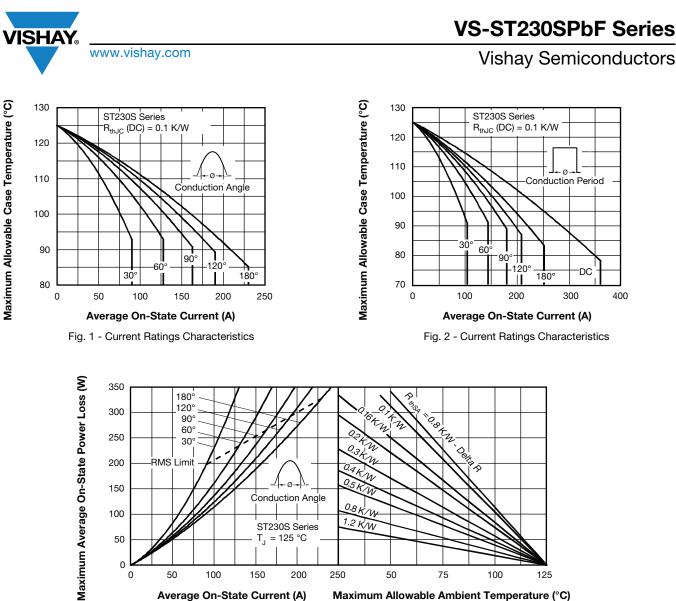
TRIGGERING								
PARAMETER	SYMBOL	т	EST CONDITIONS	VAL	UNITS			
PARAMETER	STIVIDUL		EST CONDITIONS	TYP.	MAX.	UNITS		
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	W		
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv		
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	А		
Maximum peak positive gate voltage	+ V <sub>GM</sub>		+ < 5 mg	2	0	V		
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			$r_j = r_j \max(r_j, r_p \le 5 \text{ ms})$ 5.0		.0	v
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		180	-			
DC gate current required to trigger		T <sub>J</sub> = 25 °C	Maximum required gate trigger/	90	150	mA		
		T <sub>J</sub> = 125 °C	current/voltage are the lowest	40	-			
		T <sub>J</sub> = - 40 °C	value which will trigger all units 12	2.9	-			
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	V anode to cathode applied	1.8	3.0	V		
		T <sub>J</sub> = 125 °C		1.2	-			
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/voltage not	ot 10		mA		
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.05		V		

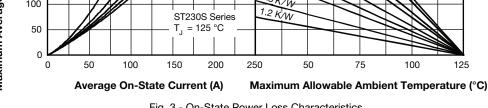
THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.10	- к/W	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	C-hs Mounting surface, smooth, flat and greased			
Mounting torque, $\pm$ 10 %		Non-lubricated threads	31 (275)	N⋅m	
Mounting torque, ± 10 %		Lubricated threads	24.5 (210)	(lbf · in)	
Approximate weight			280	g	
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-2	209AB)	

	ON			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012		
120°	0.019	0.020		
90°	0.025	0.027	$T_J = T_J maximum$	K/W
60°	0.036	0.037		
30°	0.060	0.060		

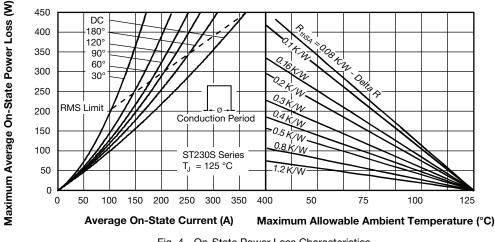
Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC













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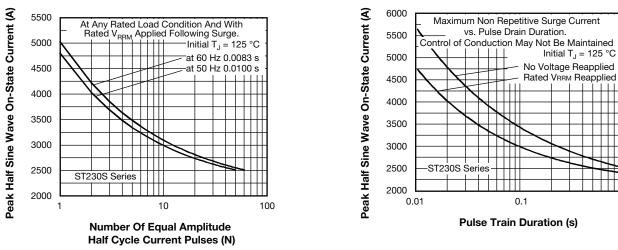


Fig. 5 - Maximum Non-Repetitive Surge Current



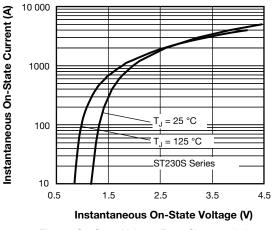
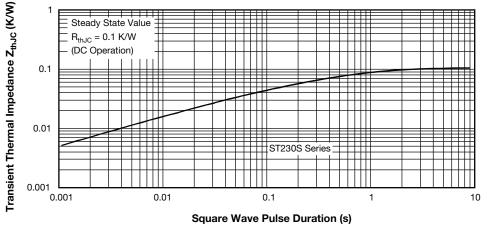
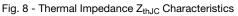


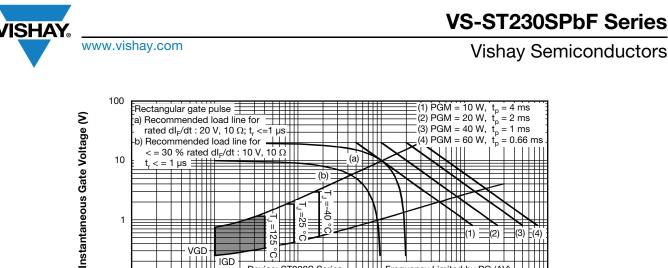
Fig. 7 - On-State Voltage Drop Characteristics





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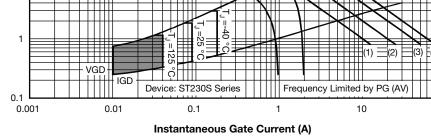


Fig. 9 - Gate Characteristics

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## **ORDERING INFORMATION TABLE**

Device code	vs-	ST	23	0	S	16	Ρ	0	PbF
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 -	Thy	ristor	niconduo art num!		oduct			
	<u> </u>			er grade					
	5 -	S =	compre	ssion bo	onding s	stud			
	6 -	Volt	age coo	de x 100	= V <sub>RRM</sub>	<sub>1</sub> (see V	oltage I	Ratings	table)
	7 -	P =	stud ba	se 3/4"-	16UNF2	2A threa	ads		
	8 -	0 =	eyelet t	erminals	s (gate a	and auxi	liary ca	thode le	eads)
		1 =	fast-on	terminal	s (gate	and aux	kiliary ca	athode	leads)
	9 -	Nor	ne = stai	ndard pr	oductio	n			
	-	Pbl	= = lead	(Pb)-fre	e				

Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95082			

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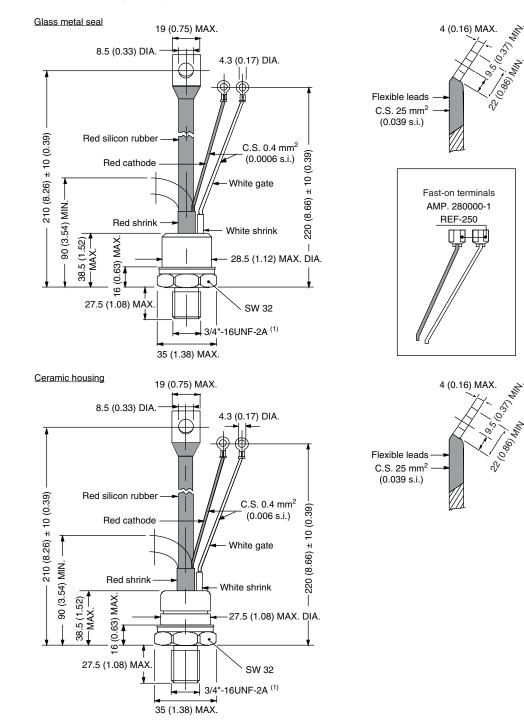
NI.

NIN,



#### **DIMENSIONS** in millimeters (inches)

www.vishay.com



#### Note

<sup>(1)</sup> For metric device: M16 x 1.5 - length 21 (0.83) maximum

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